04-19-02

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of	Group Art Unit:
CHEN, Ling and CAO, Wei	Examiner: Not Yet Assigned
Application No.: 10/050,654	**INFORMATION DISCLOSURE STATEMENT**
Filing Date: January 16, 2002	
For: **METHOD FOR GROWING THIN FILMS BY CATALYTIC ENHANCEMENT**	

CERTIFICATE OF MAILING

I hereby certify that the correspondence enclosed herein is being deposited as first class mail with the United States Postal Service on this date April 17, 2002, in an envelope addressed to: Asst. Commissioner for Patents, Washington, D.C. 20231.

By: _____
Teri L.Nelmark

Box IDS
Asst. Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Applicant submits herewith patents, publications or other information (attached hereto and listed on the attached Form PTO-1449) of which he is aware, pursuant to his duty to disclose in accordance with 37 C.F.R. § 1.56.

This Information Disclosure Statement is filed before the mailing of the first Office Action on the merits as set forth in 37 C.F.R. § 1.97.

A list of the patent(s) or publication(s) is set forth on the attached Form PTO-1449 (Modified). A copy of each of the items listed on form PTO-1449 is supplied herewith.

A concise explanation of relevance of the items listed on PTO-1449 is not given. The Examiner is reminded that a "concise explanation of the relevance" of the submitted prior art "may be nothing more than identification of the particular figure or paragraph of the patent or publication which has some relation to the claimed invention," MPEP § 609.

While the information and references disclosed in this Information Disclosure Statement may be "material" pursuant to 37 C.F.R. § 1.56, it is not intended to constitute

an admission that any patent, publication or other information referred to therein is "prior art" for this invention unless specifically designated as such.

In accordance with 37 C.F.R. § 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 C.F.R. § 1.56(a) exists. Furthermore, pursuant to 37 C.F.R. § 1.97(h), the filing of this Information Disclosure Statement shall not be construed to be an admission that the information cited in this statement is, or is considered to be, material to patentability, as defined in 1.56(b). It is submitted that the Information Disclosure Statement is in compliance with 37 C.F.R. § 1.98 and MPEP § 609 and the Examiner is respectfully requested to consider the listed references.

The Commissioner is hereby authorized to charge any additional fees or credit overpayment to our Deposit Account No. 04-0822.

Respectfully submitted,

DERGOSITS & NOAH LLP

Dated: April 17, 2002

By: _____
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PATENT

Sheet 1 of 1

FORM PTO-1449 (Rev. 7-80) U.S. Dept. of Commerce Patent and Trademark Office	Atty. Docket No. 422.05	Appl. No. 10/050,654
LIST OF REFERENCES CITED BY APPLICANT	Applicant: CHEN, Ling, et al	
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* Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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